

DIGITRON SEMICONDUCTORS

**2N1842-2N1850A
TR1010-TR9010**

SILICON CONTROLLED RECTIFIER

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).
Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|--------------|-------------|------------------|
| RMS on-state current @ $T_c = 80^\circ\text{C}$ | $I_{T(RMS)}$ | 16 | A |
| Mean on-state current @ $T_c = 80^\circ\text{C}$ | $I_{T(AV)}$ | 10 | A |
| Non-repetitive surge peak on-state current @ $T_j \leq 125^\circ\text{C}$ $t = 8.3\text{ms}$ $t = 10\text{ms}$ | I_{TSM} | 157 150 | A |
| I ² t for fusing @ $T_j \leq 125^\circ\text{C}$, $t = 10\text{ms}$ | I^2t | 112.5 | A ² s |
| Critical rate of rise of on-state current | di/dt | 100 | A/ μs |
| Operating junction temperature range | T_j | -40 to +150 | $^\circ\text{C}$ |
| Storage temperature range | T_{stg} | -40 to +125 | $^\circ\text{C}$ |

VOLTAGE RATINGS

| $T_j = 125^\circ\text{C}$ | 2N 1842(A) | 2N 1843(A) | 2N 1844(A) | 2N 1846(A) | 2N 1848(A) | 2N 1849(A) | 2N 1850(A) | TR 6010 | TR 7010 | TR 8010 | TR 9010 | TR 1010 | TR 1110 | TR 1210 |
|---------------------------|---------------|---------------|---------------|---------------|---------------|---------------|---------------|------------|------------|------------|------------|------------|------------|------------|
| VOLTS | | | | | | | | | | | | | | |
| $V_{DRM} = V_{RRM}$ | 25 | 50 | 100 | 200 | 300 | 400 | 500 | 600 | 700 | 800 | 900 | 1000 | 1100 | 1200 |

THERMAL RESISTANCE

| Thermal resistance | Symbol | Value | Unit |
|-------------------------|---------------|-------|--------------------|
| Junction to case for DC | $R_{th(j-c)}$ | 2 | $^\circ\text{C/W}$ |
| Case to heatsink | $R_{th(c-h)}$ | 0.4 | $^\circ\text{C/W}$ |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Value | | | Unit | Test conditions | | | |
|------------------------------------|-----------|-------|-----|-----|------------------|---|---|---------------------|-----------------------------------|
| | | Min | Typ | Max | | | | | |
| Gate trigger current | I_{GT} | - | - | 80 | mA | $T_j = 25^\circ\text{C}$ | $V_D = 12\text{V}$ | $R_L = 33\Omega$ | $t_p \geq 20\mu\text{s}$ |
| Gate trigger voltage | V_{GT} | - | - | 3 | V | $T_j = 25^\circ\text{C}$ | $V_D = 12\text{V}$ | $R_L = 33\Omega$ | $t_p \geq 20\mu\text{s}$ |
| Peak gate voltage | V_{GD} | 0.25 | - | - | | $T_j = 125^\circ\text{C}$ | $V_D = V_{DRM}$ | $R_L = 3.3\Omega$ | |
| Holding current | I_H | - | 20 | - | mA | $T_j = 25^\circ\text{C}$ | $I_T = 0.5\text{A}$ | Gate open | |
| Peak on-state voltage | V_{TM} | - | - | 2.2 | V | $T_j = 25^\circ\text{C}$ | $I_{TM} = 30\text{A}$ | $t_p = 10\text{ms}$ | |
| Maximum off-state current | I_{DRM} | - | - | 5 | mA | $T_j = 125^\circ\text{C}$ | V_{DRM} specified | | |
| Maximum off-state current | I_{RRM} | - | - | 5 | mA | $T_j = 125^\circ\text{C}$ | V_{RRM} specified | | |
| Turn on time | t_{gt} | - | 2 | - | μs | $T_j = 25^\circ\text{C}$ $I_G = 200\text{mA}$ | $I_T = 30\text{A}$ $di_G/dt = 2\text{A}/\mu\text{s}$ | $V_D = V_{DRM}$ | |
| Turn off time | t_q | - | 100 | - | μs | $T_j = 125^\circ\text{C}$ $di_R/dt = 30\text{A}/\mu\text{s}$ | $I_T = 10\text{A}$ $dv/dt = 20\text{V}/\mu\text{s}$ | $V_R = 30\text{V}$ | $V_D = 0.67 V_{DRM}$ Gate open |
| Critical rise of off-state voltage | dv/dt | 100 | - | - | V/ μs | $T_j = 125^\circ\text{C}$ | Linear slope up to $0.67 V_{DRM}$ specified | | |

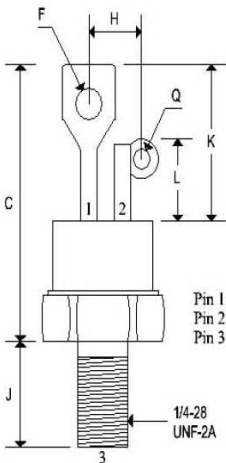
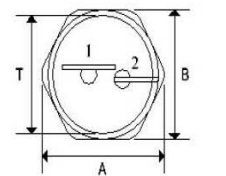
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MECHANICAL CHARACTERISTICS

| | |
|-----------------|---------------|
| Case | TO-48 |
| Marking | Alpha-numeric |
| Polarity | Cathode |



Pin 1: Cathode
Pin 2: Gate
Pin 3: Anode

1/4-28
UNF-2A

| | TO-48 | | | |
|---|--------|-------|-------------|--------|
| | Inches | | Millimeters | |
| | Min | Max | Min | Max |
| A | 0.604 | 0.614 | 15.340 | 15.600 |
| B | 0.551 | 0.559 | 14.000 | 14.200 |
| C | 1.050 | 1.190 | 2.670 | 30.230 |
| F | 0.135 | 0.160 | 3.430 | 4.060 |
| H | - | 0.265 | - | 6.730 |
| J | 0.420 | 0.455 | 10.670 | 11.560 |
| K | 0.620 | 0.670 | 15.750 | 17.020 |
| L | 0.300 | 0.350 | 7.620 | 8.890 |
| Q | 0.055 | 0.085 | 1.400 | 2.160 |
| T | 0.501 | 0.505 | 12.730 | 12.830 |

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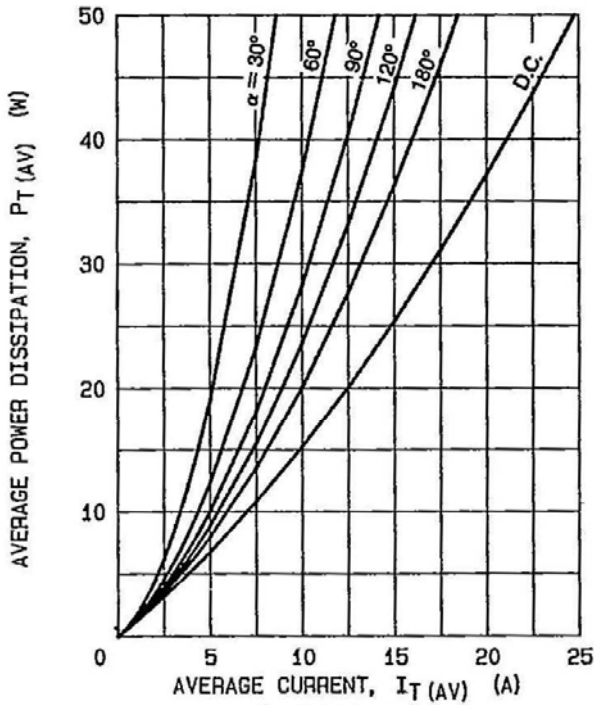


FIG.1 - MAXIMUM ON-STATE POWER DISSIPATION FOR SINUSOIDAL CURRENT WAVEFORM

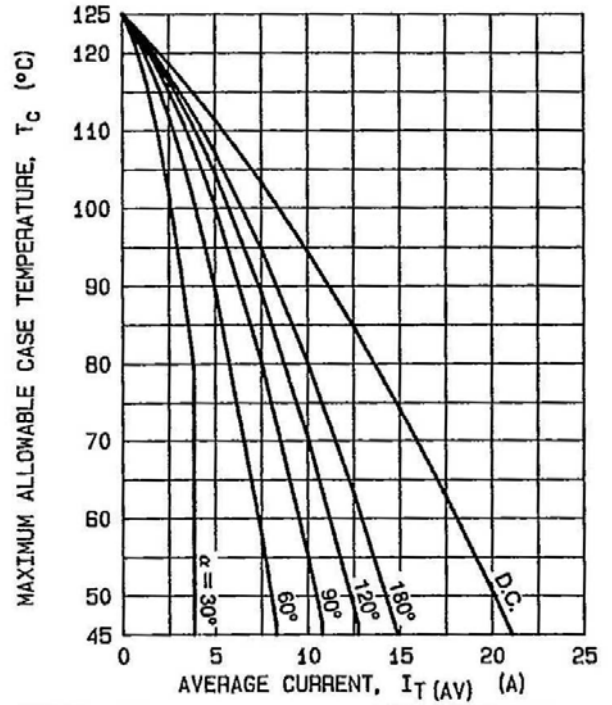


FIG.2 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR SINUSOIDAL CURRENT WAVEFORM

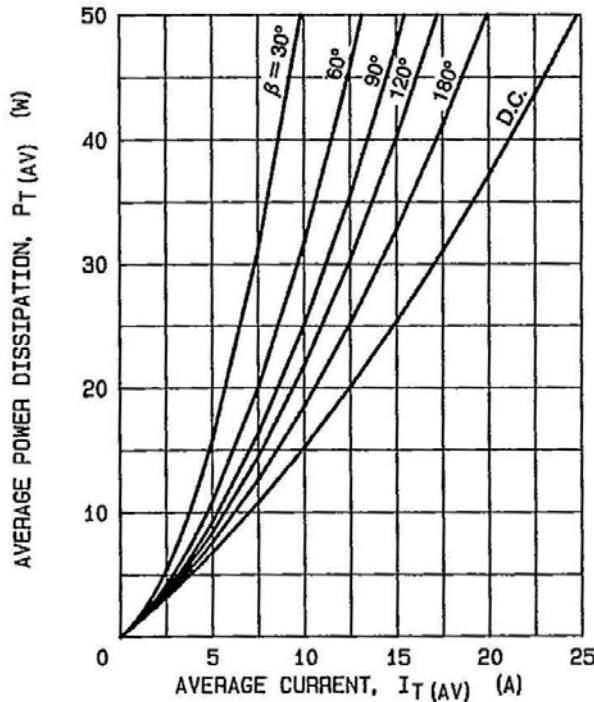
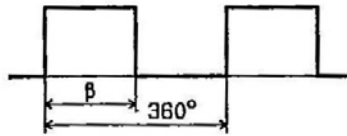


FIG.3 - MAXIMUM ON-STATE POWER DISSIPATION FOR RECTANGULAR CURRENT WAVEFORM

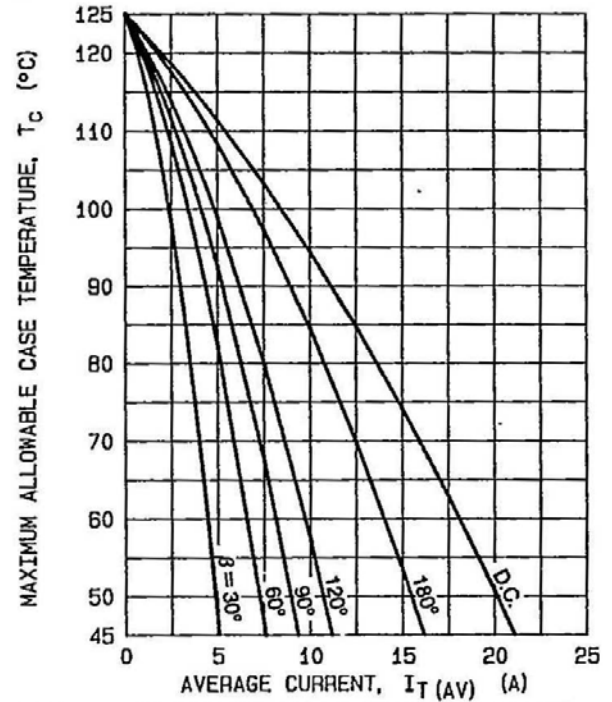


FIG.4 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR RECTANGULAR CURRENT WAVEFORM

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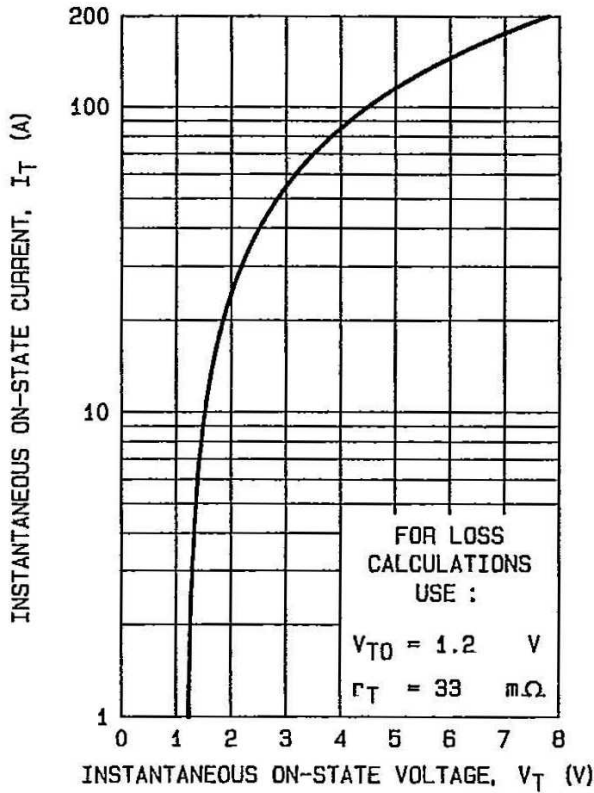


FIG.5 - MAXIMUM ON-STATE CONDUCTION CHARACTERISTIC ($T_J = 125^\circ\text{C}$).

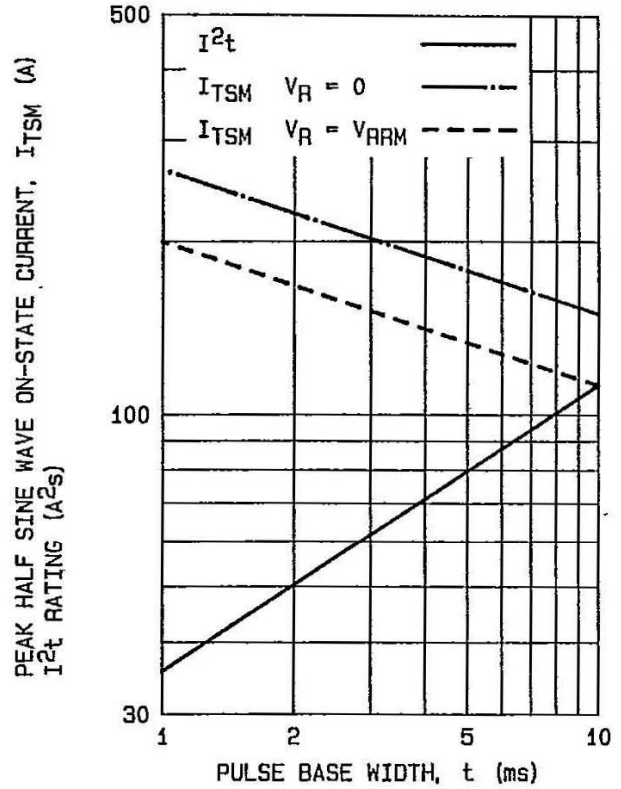


FIG.6 - NON REPETITIVE SUB-CYCLE SURGE ON-STATE CURRENT AND I^2t RATING (INITIAL $T_J = 125^\circ\text{C}$).

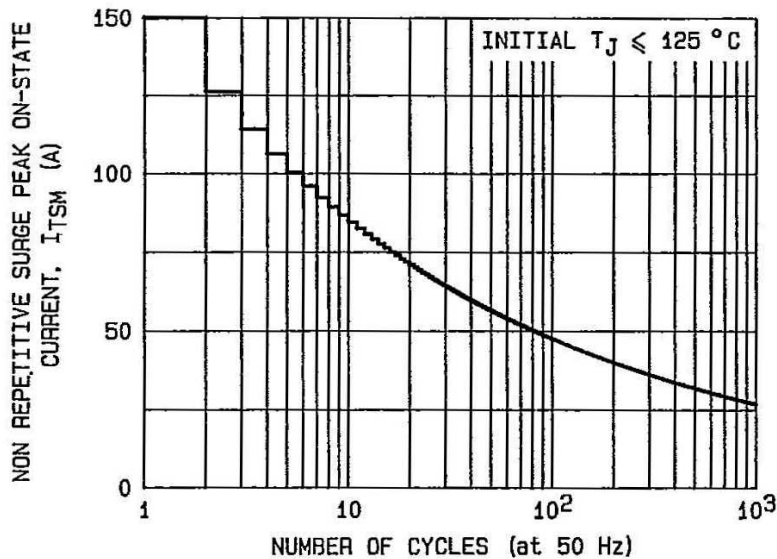


FIG.7 - NON REPETITIVE SURGE PEAK ON-STATE CURRENT VERSUS NUMBER OF CYCLES.

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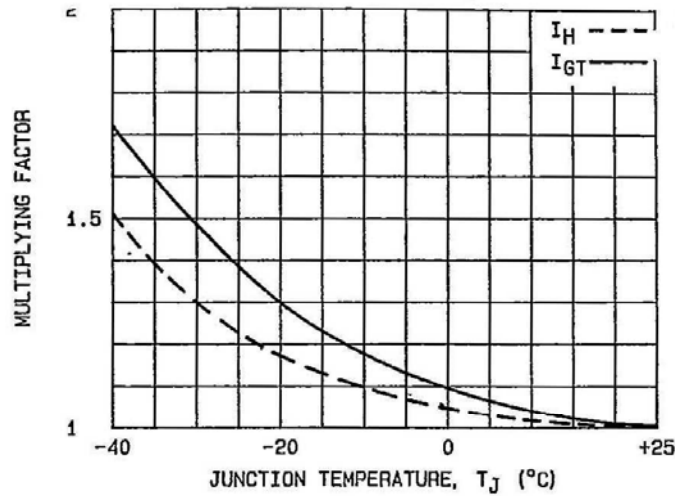


FIG.8 - RELATIVE VARIATION OF GATE TRIGGER CURRENT AND HOLDING CURRENT VERSUS JUNCTION TEMPERATURE.

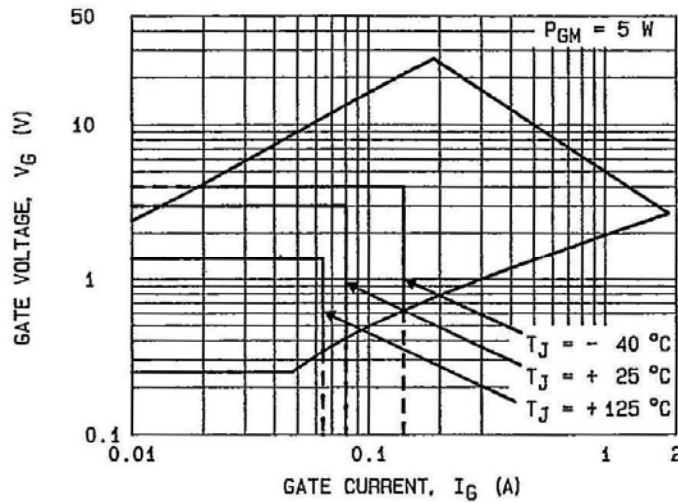


FIG.9 - GATE TRIGGER CHARACTERISTICS.

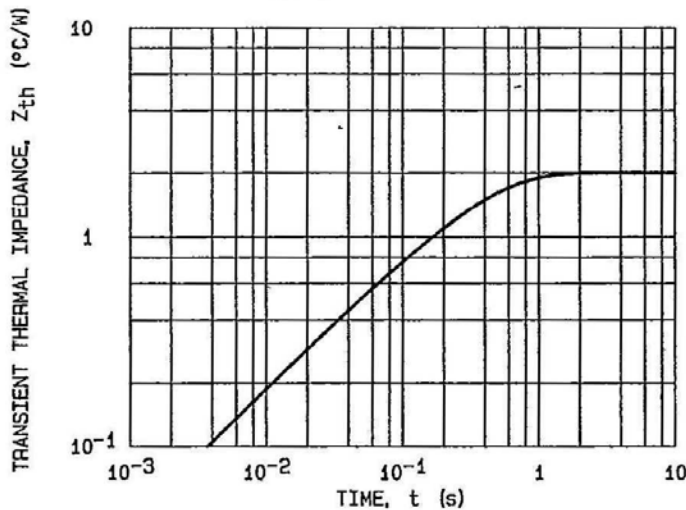


FIG.10 - TRANSIENT THERMAL IMPEDANCE JUNCTION TO CASE.

| Conduction angle (α, β) | Effective thermal resistance ($^{\circ}\text{C}/\text{W}$) junction to case | |
|--------------------------------------|---|-------------|
| | Sinusoidal | Rectangular |
| 180° | 2.23 | 2.18 |
| 120° | 2.31 | 3.09 |
| 90° | 2.47 | 3.50 |
| 60° | 2.88 | 3.91 |
| 30° | 3.71 | 4.94 |